



NDDL01N60Z-1G Information



For Reference Only

Part Number NDDL01N60Z-1G Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 0.8A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NDDL01N60Z-1G Specifications

Manufacturer Part Number NDDL01N60Z-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 800mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 50µA Gate Charge (Qg) (Max) @ Vgs 4.9nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 92pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 26W (Tc) Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C800mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs4.9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds92pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)26W (Tc)Rds On (Max) @ Id, Vgs15 Ohm @ 400mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 800mA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 4.9nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C800mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5 V @ 50μAGate Charge (Qg) (Max) @ Vgs4.9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds92pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)26W (Tc)Rds On (Max) @ Id, Vgs15 Ohm @ 400mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
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Current - Continuous Drain (Id) @ 25°C Brive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature Supplier Device Package IPAK (TO-251) Package / Case 800mA (Ta) 92pF @ 25V 4.9nC @ 10V 92pF @ 25V 25V 25V 25V 25V 25V 25V 26W (Tc) 15 Ohm @ 400mA, 10V 15 Ohm @	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs4.9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds92pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)26W (Tc)Rds On (Max) @ Id, Vgs15 Ohm @ 400mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	600V
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Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 92pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
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Vgs (Max) ± 30 VFET Feature-Power Dissipation (Max) 26 W (Tc)Rds On (Max) @ Id, Vgs 15 Ohm @ 400 mA, 10 VOperating Temperature -55° C $\sim 150^{\circ}$ C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAK (TO-251)Package / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	4.9nC @ 10V
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Power Dissipation (Max) Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 15 Ohm @ 400mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	26W (Tc)
Mounting Type Through Hole Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	15 Ohm @ 400mA, 10V
Supplier Device Package IPAK (TO-251) Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	IPAK (TO-251)
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NDDL01N60Z-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NDDL01N60Z-1G Payment Methods



















NDDL01N60Z-1G Shipping Methods













If you have any question about NDDL01N60Z-1G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com